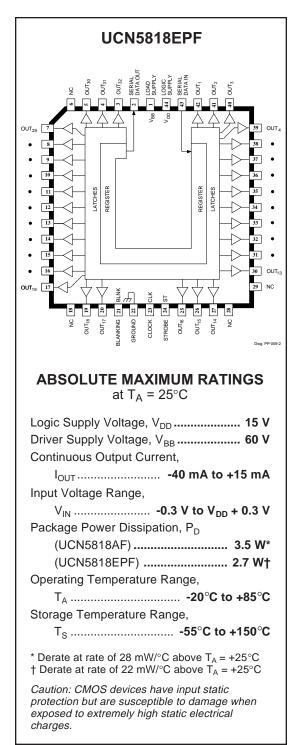
5818-F

BiMOS II 32-BIT SERIAL-INPUT, LATCHED SOURCE DRIVERS WITH ACTIVE-DMOS PULL-DOWNS



Designed primarily for use with vacuum-fluorescent displays, the UCN5818AF and UCN5818EPF smart power BiMOS II drivers combine CMOS shift registers, data latches, and control circuitry, with bipolar high-speed sourcing outputs and DMOS active pull-down circuitry. The high-speed shift register and data latches allow direct interfacing with microprocessor LSI-based systems. A CMOS serial data output enables cascade connections in applications requiring additional drive lines. Both devices feature 60 V and -40 mA output ratings, allowing them to be used in many other peripheral power driver applications.

These smart power drivers have been designed with BiMOS II logic for improved data entry rates. With a 5 V supply, they will typically operate above 5 MHz. At 12 V, significantly higher speeds are obtained. Use of these devices with TTL may require the use of appropriate pull-up resistors to ensure an input logic high. All devices can be operated over the ambient temperature range of -20°C to +85°C. The UCN5818AF is supplied in a 40-pin plastic dual in-line package with 0.600" (15.24 mm) row spacing. A copper lead frame, reduced supply current requirement, and low output saturation voltage permits operation with minimum junction temperature rise. The 'A' package allows all 32 outputs to be operated at -25 mA continuously over the operating temperature range.

For high-density packaging applications, the UCN5818EPF is furnished in a 44-lead plastic chip carrier (quad pack) for surface mounting on solder lands with 0.050" (1.27 mm) centers. The PLCC allows -25 mA continuous operation of all outputs simultaneously at ambient temperatures to 60°C. Similar devices are available as the UCN5810AF/LWF (10 bits), UCN5811A (12 bits), and UCN5812AF/ EPF (20 bits).

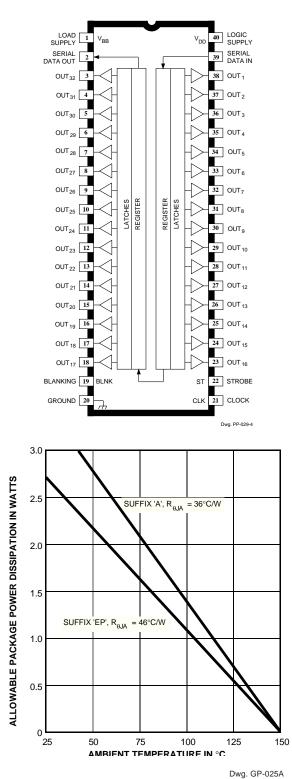
FEATURES

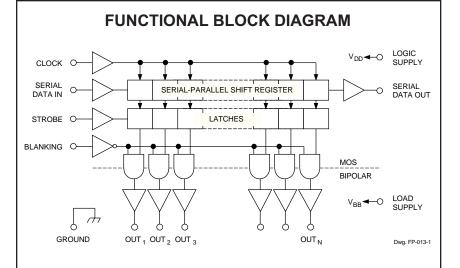
- 60 V Source Outputs
- High-Speed Source Drivers
- To 3.3 MHz Data Input Rate
- Low-Output Saturation Voltages
- Active DMOS Pull-Downs
- Low-Power CMOS Logic and Latches
- Reduced Supply Current Requirements
- Improved Replacements for SN75518N/FN

Always order by complete part number, e.g., UCN5818EPF.

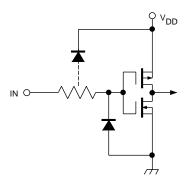


UCN5818AF



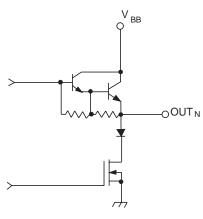


TYPICAL INPUT CIRCUIT



Dwg. EP-010-5

TYPICAL OUTPUT DRIVER



Dwg. No. A-14,219

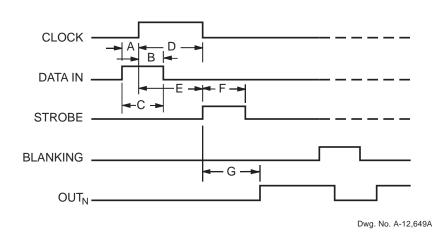


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ELECTRICAL CHARACTERISTICS at $T_A = +25^{\circ}C$, $V_{BB} = 60$ V unless otherwise noted.

			Limits @ V _{DD} = 5 V			Limits			
Characteristic	Symbol	Test Conditions	MIn.	Тур.	Max.	Min.	Тур.	Max.	Units
Output Leakage Current	I _{CEX}	V _{OUT} = 0 V, T _A = +70°C	—	-5.0	-15	—	-5.0	-15	μΑ
Output Voltage	V _{OUT(1)}	I _{OUT} = -25 mA	58	58.5	_	58	58.5	_	V
	V _{OUT(0)}	I _{OUT} = 1 mA	-	2.0	3.0	—	_	_	V
		I _{OUT} = 2 mA	-		_	—	2.0	3.5	V
Output Pull-Down Current	I _{OUT(0)}	$V_{OUT} = 5 V \text{ to } V_{BB}$	2.0	3.5		—	_		mA
		V_{OUT} = 20 V to V_{BB}	-	_		8.0	13		mA
Input Voltage	V _{IN(1)}		3.5	_	5.3	10.5	_	12.3	V
	V _{IN(0)}		-0.3	_	+0.8	-0.3	_	+0.8	V
Input Current	I _{IN(1)}	$V_{IN} = V_{DD}$	-	0.05	0.5	-	0.1	1.0	μΑ
	I _{IN(0)}	V _{IN} = 0.8 V	—	-0.05	-0.5	_	-0.1	-1.0	μΑ
Serial Data Output Voltage	V _{OUT(1)}	I _{OUT} = -200 μA	4.5	4.7	_	11.7	11.8	_	V
	V _{OUT(0)}	I _{OUT} = 200 μA	—	200	250	—	100	200	mV
Maximum Clock Frequency	f _{clk}		3.3	5.0	_	—	7.5	_	MHz
Supply Current	I _{DD(1)}	All Outputs High	—	100	300	_	200	500	μΑ
	I _{DD(0)}	All Outputs Low	-	100	300	—	200	500	μA
	I _{BB(1)}	Outputs High, No Load	-	3.0	6.0	—	3.0	6.0	mA
	I _{BB(0)}	Outputs Low	—	10	100	-	10	100	μΑ
Blanking to Output Delay	t _{PHL}	C _L = 30 pF, 50% to 50%	-	2000		—	1000	_	ns
	t _{PLH}	C _L = 30 pF, 50% to 50%	-	1000	_	—	850	_	ns
Output Fall Time	t _f	C _L = 30 pF, 90% to 10%	- 1	1450		—	650		ns
Output Rise Time	t _r	C _L = 30 pF, 10% to 90%	-	650	_	—	700		ns

Negative current is defined as coming out of (sourcing) the specified device terminal.



TIMING CONDITIONS

(T_A = +25°C, V_{DD} = 5.0 V, Logic Levels are V_{DD} and Ground)

A. Minimum Data Active Time Before Clock Pulse (Data Set-Up Time)	75 ns
B. Minimum Data Active Time After Clock Pulse	
(Data Hold Time)	75 ns
C. Minimum Data Pulse Width	150 ns
D. Minimum Clock Pulse Width	150 ns
E. Minimum Time Between Clock Activation and Strobe	300 ns
F. Minimum Strobe Pulse Width	100 ns
G. Typical Time Between Strobe Activation and	
Output Transition	500 ns

Serial Data present at the input is transferred to the shift register on the logic "0" to logic "1" transition of the CLOCK input pulse. On succeeding CLOCK pulses, the registers shift data information towards the SERIAL DATA OUTPUT. The SERIAL DATA must appear at the input prior to the rising edge of the CLOCK input waveform.

Information present at any register is transferred to the respective latch when the STROBE is high (serial-to-parallel conversion). The latches will continue to accept new data as long as the STROBE is held high. Applications where the latches are bypassed (STROBE tied high) will require that the BLANKING input be high during serial data entry.

When the BLANKING input is high, the output source drivers are disabled (OFF); the DMOS sink drivers are ON, the information stored in the latches is not affected by the BLANKING input. With the BLANKING input low, the outputs are controlled by the state of their respective latches.

TRUTH TABLE

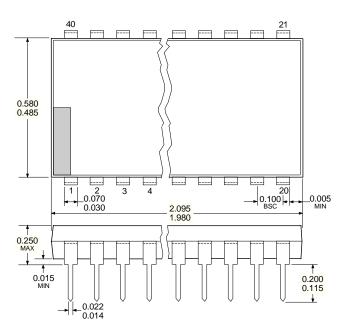
Serial		Shift Register Contents					Serial		Latch Contents						Output Contents							
Data Input	Clock Input	Ι ₁	I ₂	I ₃		I _{N-1}	I _N	Data Output	Strobe Input	I ₁	I ₂	I ₃		I _{N-1}	I _N	Blanking	I ₁	l ₂	I ₃		I _{N-1}	I _N
н	Г	н	R ₁	R ₂		R _{N-2}	R _{N-1}	R _{N-1}														
L	7	L	R_1	R_2		R _{N-2}	R _{N-1}	R _{N-1}														
х	L	R ₁	R_2	R_3		R _{N-1}	R _N	R _N														
		Х	Х	Х		Х	Х	Х	L	R ₁	R_2	R_3		R _{N-1}	R _N							
		Р ₁	P_2	P ₃		P _{N-1}	P _N	P _N	Н	P ₁	P ₂	P ₃		P _{N-1}	P _N	L	P ₁	P ₂	Ρ3		P _{N-1}	P _N
										Х	Х	Х		Х	Х	Н	L	L	L		L	L

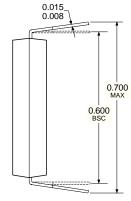
L = Low Logic Level H = High Logic Level X = Irrelevant P = Present State R = Previous State



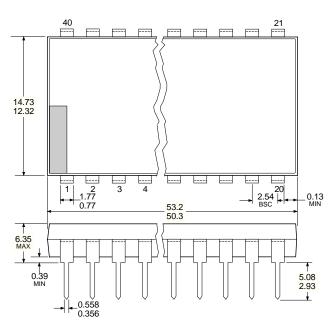
UCN5818AF

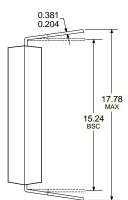
Dimensions in Inches (controlling dimensions)





Dimensions in Millimeters (for reference only)



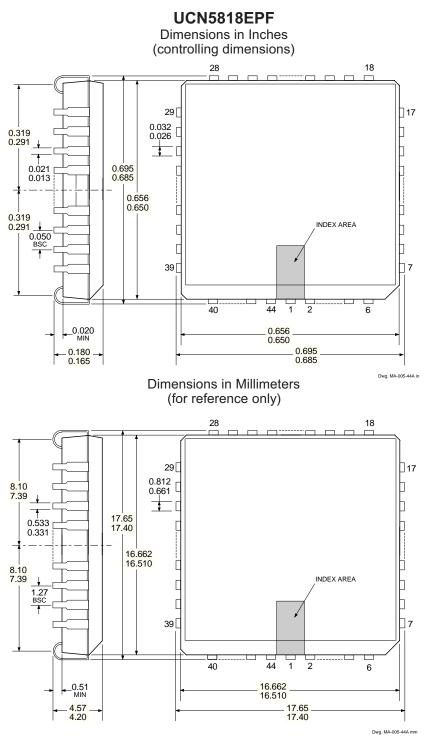


Dwg. MA-003-40 in

Dwg. MA-003-40 mm

NOTES: 1. Exact body and lead configuration at vendor's option within limits shown.

- 2. Lead spacing tolerance is non-cumulative.
 - 3. Lead thickness is measured at seating plane or below.



NOTES: 1. Exact body and lead configuration at vendor's option within limits shown.

2. Lead spacing tolerance is non-cumulative.



115 Northeast Cutoff, Box 15036 Worcester, Massachusetts 01615-0036 (508) 853-5000

BiMOS II (Series 5800) & DABiC IV (Series 6800) INTELLIGENT POWER INTERFACE DRIVERS SELECTION GUIDE

Function	Output F	Ratings *	Part Number †						
SERIAL-INPUT LATCHED DRIVERS									
8-Bit (saturated drivers)	-120 mA	50 V‡	5895						
8-Bit	350 mA	50 V	5821						
8-Bit	350 mA	80 V	5822						
8-Bit	350 mA	50 V‡	5841						
8-Bit	350 mA	80 V‡	5842						
9-Bit	1.6 A	50 V	5829						
10-Bit (active pull-downs)	-25 mA	60 V	5810-F and 6809/10						
12-Bit (active pull-downs)	-25 mA	60 V	5811 and 6811						
20-Bit (active pull-downs)	-25 mA	60 V	5812-F and 6812						
32-Bit (active pull-downs)	-25 mA	60 V	5818-F and 6818						
32-Bit	100 mA	30 V	5833						
32-Bit (saturated drivers)	100 mA	40 V	5832						
PARA	LLEL-INPUT LATCHED D	RIVERS							
4-Bit	350 mA	50 V‡	5800						
8-Bit	-25 mA	60 V	5815						
8-Bit	350 mA	50 V‡	5801						
SPE	ECIAL-PURPOSE FUNCT	IONS							
Unipolar Stepper Motor Translator/Driver	1.25 A	50 V‡	5804						
Addressable 28-Line Decoder/Driver	450 mA	30 V	6817						

* Current is maximum specified test condition, voltage is maximum rating. See specification for sustaining voltage limits. Negative current is defined as coming out of (sourcing) the output.

† Complete part number includes additional characters to indicate operating temperature range and package style.

‡ Internal transient-suppression diodes included for inductive-load protection.

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